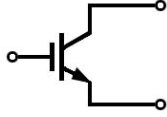
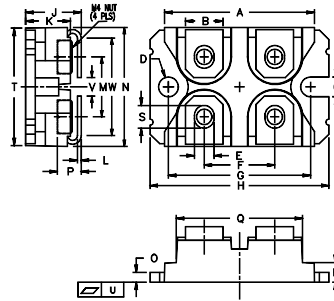


SG75S12S

Discrete IGBTs



Dimensions SOT-227(ISOTOP)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033

	I _C	V _{CE}
	A	V
SG75S12S	75	1200

Maximum Rated Values

(T_{vj} = 25°C, unless specified otherwise)

Parameter	Symbol	Conditions	Values	Unit
Collector-Emitter Voltage	V _{CEs}	V _{GE} shorted	1200	V
DC Collector Current	I _C	T _{hs} = 70°C	75	A
Peak Collector Current	I _{CM}	Pulse: t _p = 1ms, T _{hs} = 70°C	150	A
Gate Emitter Voltage	V _{GES}		±20	V
Total Power Dissipation	P _{tot}	T _{hs} = 25°C per switch	340	W
IGBT Switching SOA	SwSOA	I _C = 150A, V _{CEM} = 1200V, V _{CC} ≤ 1000V, V _{GE} = ±15V, T _{vj} = 125°C voltages measured on auxiliary terminals		
IGBT Short Circuit SOA	SCSOA	V _{CC} = 900V, V _{CEM} = 1200V, t _p = 10μs, V _{GE} = ±15V, T _{vj} = 125°C		
DC Forward Current	I _F		75	A
Peak Forward Current	I _{FM}	Pulse: t _p = 1ms, T _{hs} = 70°C	150	A

Maximum Rated Values (cont.)

(T_{vj} = 25°C, unless specified otherwise)

Parameter	Symbol	Conditions	Values	Unit
Junction Temperature	T _{vj}		-40 ~ 150	°C
Storage Temperature	T _{tstg} / T _{cop}		-40 ~ 125	°C
Isolation Voltage	V _{iso}	1min, f = 50Hz	2500	V

SG75S12S

Discrete IGBTs

IGBT Characteristic Values

($T_{vj} = 25^{\circ}\text{C}$, unless specified otherwise)

Parameter	Sybmol	Conditions	min.	typ.	max.	Unit
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$	$I_C = 75\text{A}$, $V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$	2.00	2.35	V
			$T_{vj} = 125^{\circ}\text{C}$	2.20		V
Collector Cut-off Current	I_{CES}	$V_{CE} = 1200\text{V}$, $V_{GE} = 0\text{V}$, $T_{vj} = 125^{\circ}\text{C}$			6	mA
Gate-Emitter leakage Current	I_{GES}	$V_{CE} = 0\text{V}$, $V_{GE} = \pm 20\text{V}$, $T_{vj} = 125^{\circ}\text{C}$			± 500	nA
Gate-Emitter Threshold Voltage	$V_{GE(TH)}$	$I_C = 3\text{mA}$, $V_{CE} = V_{GE}$	4.5		6.5	V
Total Gate Charge	Q_{ge}	$I_C = 75\text{A}$, $V_{CE} = 600\text{V}$, $V_{GE} = -15$ to 15V		750		nC
Input Capacitance	C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		6.5		nF
Output Capacitance	C_{oes}			1.6		nF
Reverse Transfer Capacitance	C_{res}			1.4		nF
Turn-On Delay Time	$t_{d(on)}$	$I_C = 75\text{A}$, $V_{CC} = 600\text{V}$, $R_{gon} = 15\Omega$, $T_{vj} = 125^{\circ}\text{C}$, $V_{GE} = \pm 15\text{V}$		0.1		μs
Rise Time	t_r			0.05		μs
Turn-Off Delay Time	$t_{d(off)}$	$I_C = 75\text{A}$, $V_{CC} = 600\text{V}$, $R_{goff} = 15\Omega$, $T_{vj} = 125^{\circ}\text{C}$, $V_{GE} = \pm 15\text{V}$		0.50		μs
Fall Time	t_f			0.09		μs
Turn-on Switching Energy	E_{on}	$R_{gon} = 15\Omega$ $I_C = 75\text{A}$, $T_{vj} = 125^{\circ}\text{C}$, $V_{CC} = 600\text{V}$, $V_{GE} = \pm 15\text{V}$, inductive load, integrated up to: 3% V_{CE} (E_{on}), 1% I_C (E_{off})		8.5		mJ
	E_{off}			7.0		mJ
Module stray Inductance Plus to Minus	L_{sDC}				25	nH
Resistance terminal-chip	R_{CC+EE}	$T_{hs} = 25^{\circ}\text{C}$		1.25		m Ω
		$T_{hs} = 125^{\circ}\text{C}$		1.90		

* Note 1: Collector emitter saturation voltage is given at die level.

SG75S12S

Discrete IGBTs

Diode Characteristic Values

(T_j = 25°C, unless specified otherwise)

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Forward Voltage	V _F *	I _F = 75A		2.00	2.40	V
				2.00		
Reverse Recovery Current	I _{rrm}	I _F = 75A, R _{gon} = 15Ω, V _{CC} = 600V, V _{GE} = ±15V, T _{vj} = 125°C		75		A
Reverse Recovery Charge	Q _{rr}			14		μC
Reverse Recovery Time	t _{rr}			0.35		μs
Reverse Recovery Energy	E _{rec}	I _F = 75A, T _{vj} = 125°C, V _{CC} = 600V, R _{gon} = 15Ω, V _{GE} = ±15V, inductive load, fully integrated		5.5		mJ
Resistance terminal-chip	R _{CC'+EE'}			1.25		mΩ
				1.90		

* Note 2: Forward voltage is given at die level

Thermal Characteristics

(T_j = 25°C, unless specified otherwise)

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
IGBT Thermal Resistance Junction to Heatsink	R _{th j-h Igbt}	Heatsink: flatness < +/-20μm, roughness < 6μm without ridge Thermal grease: thickness: 30μm < t < 50μm			0.370	°C/W
Diode Thermal Resistance Junction to Heatsink	R _{th j-h Diode}				0.740	°C/W
Equivalent IGBT Thermal Resistance Junct. to Case	R _{th j-c Igbt}				0.235	°C/W
Equivalent Diode Thermal Resistance Junct. to Case	R _{th j-c Diode}				0.550	°C/W

SG75S12S

Discrete IGBTs

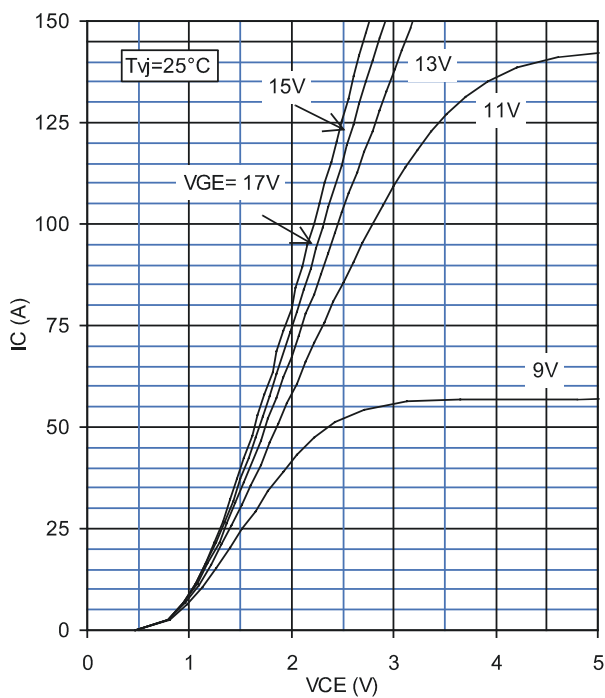


Fig. 1 Typ. Output Characteristics at $T_{vj}=25^{\circ}\text{C}$

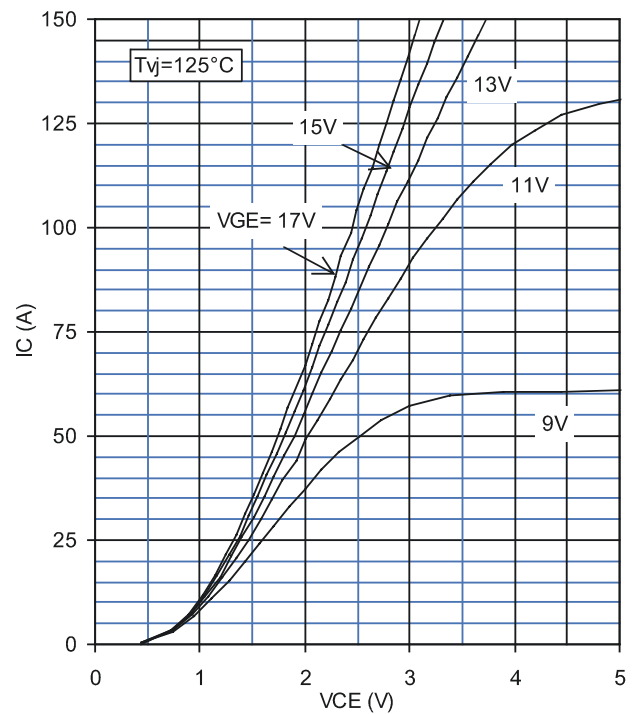


Fig. 2 Typ. Output Characteristics at $T_{vj}=125^{\circ}\text{C}$

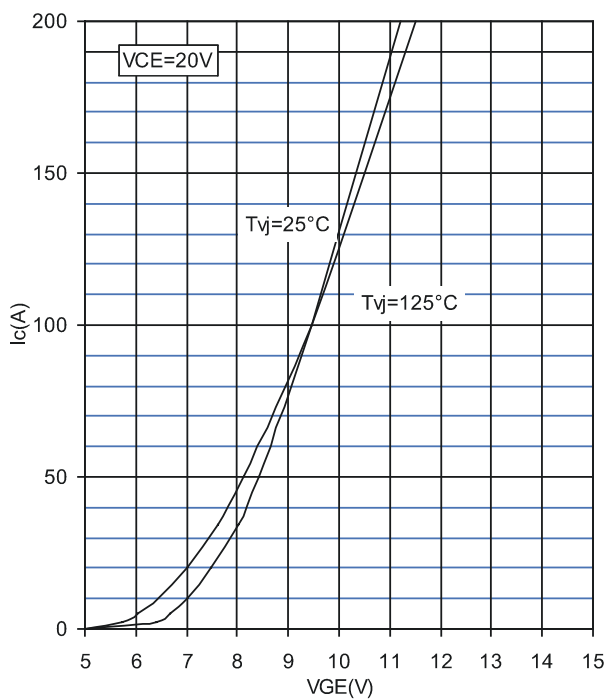


Fig. 3 Typ. Transfer Characteristics

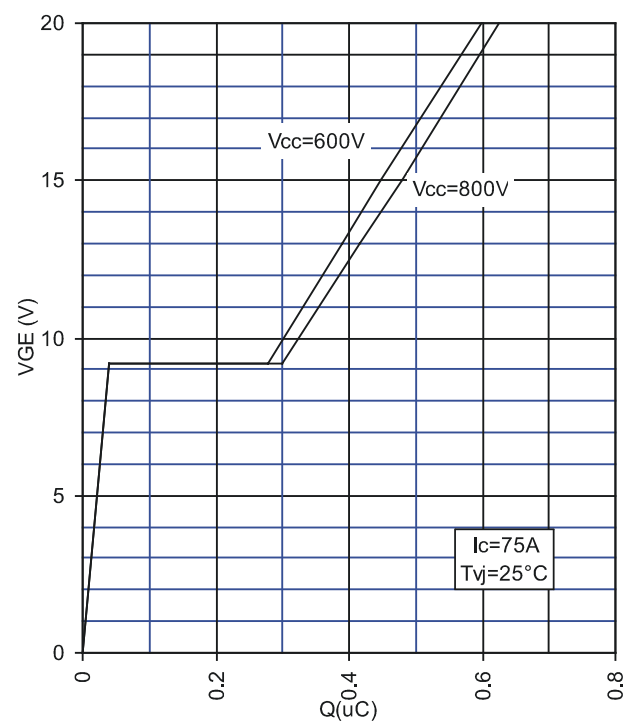


Fig. 4 Typ. Gate charge Characteristi

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Discrete IGBTs

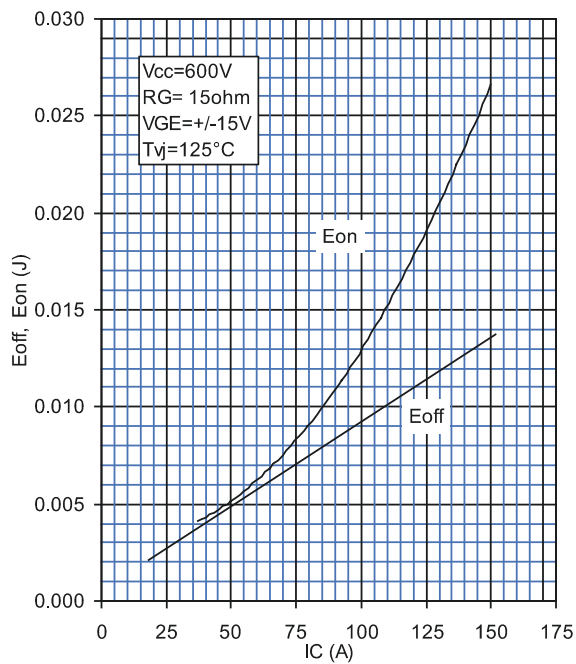


Fig. 5 Typ. Switching Energies per pulse vs on-state current

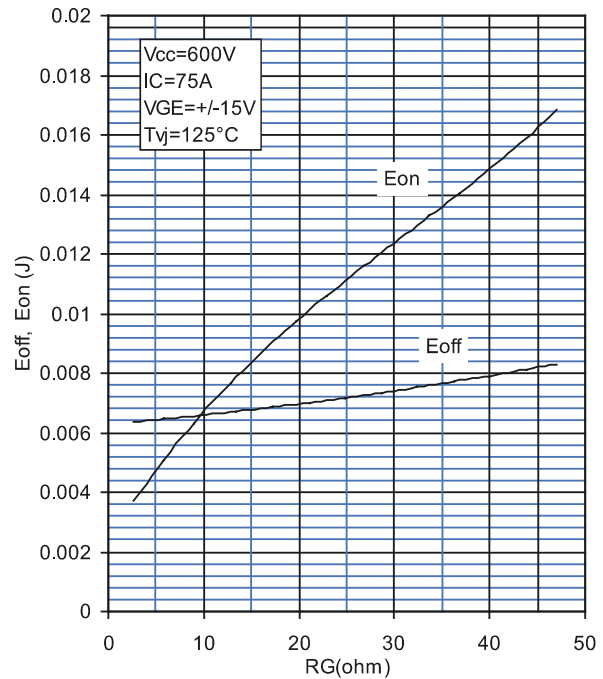


Fig. 6 Typ. Switching Energies per pulse v gate resistor

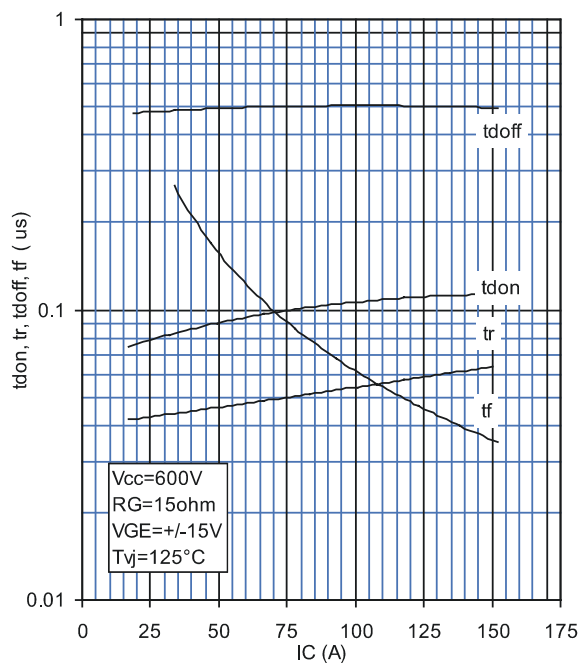


Fig. 7 Typ. Switching times vs on-state current

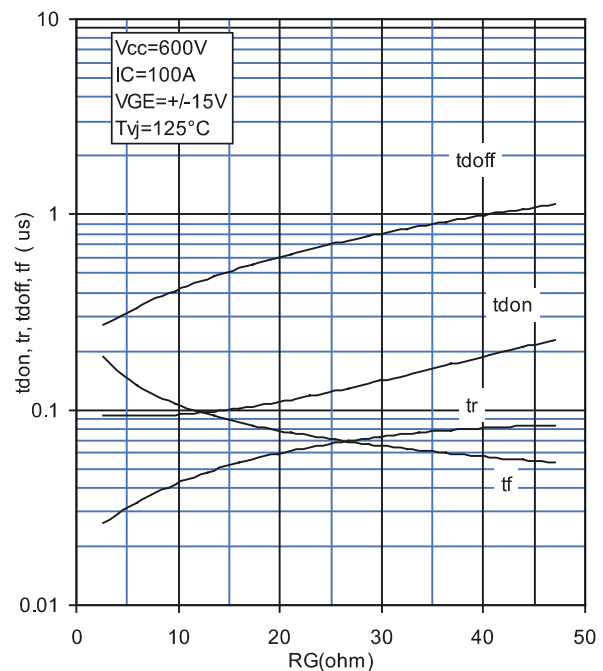


Fig. 8 Typ. Switching times vs gate resistor

SG75S12S

Discrete IGBTs

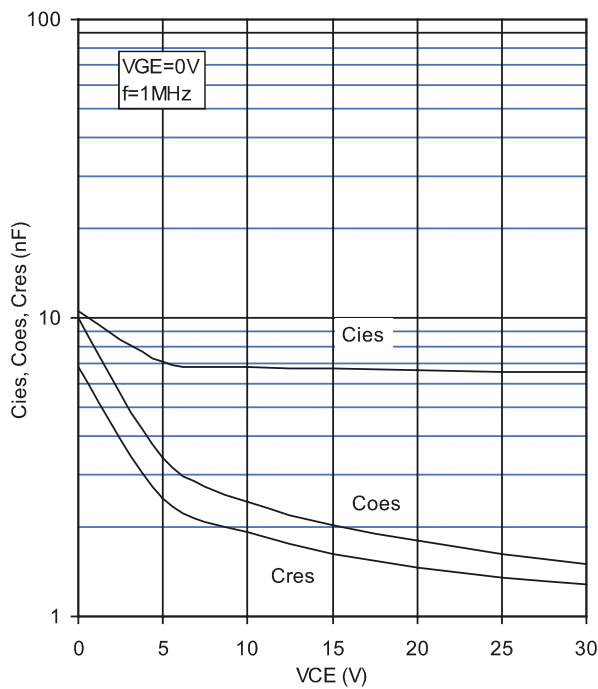


Fig. 9 Typ. Capacitances vs collector-emitter Voltage

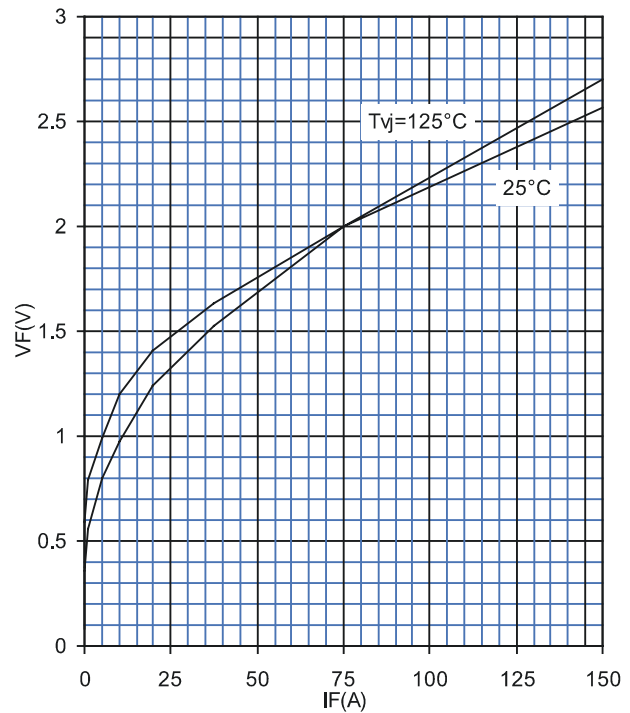


Fig. 10 Typ. Diode forward Characteristics

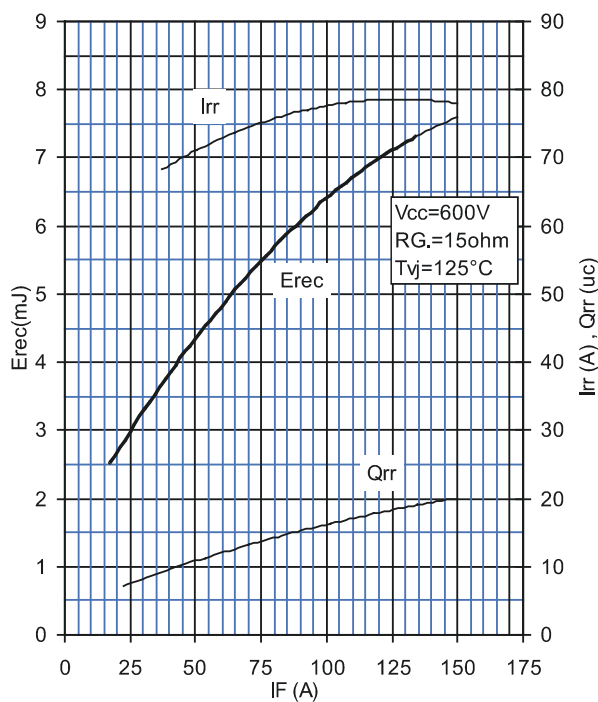


Fig. 11 Typ. Reverse Recovery Characteristics vs forward current

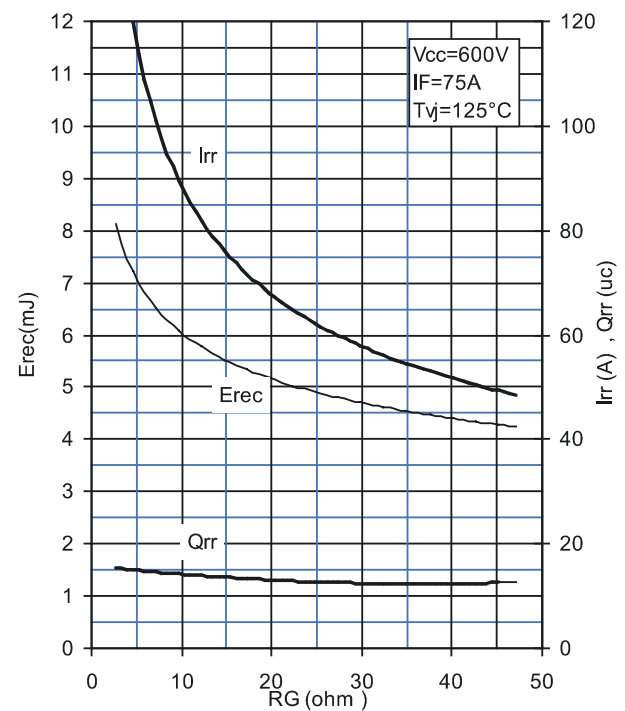


Fig. 12 Typ. Reverse Recovery Characteristics vs gate resistor

SG75S12S

Discrete IGBTs

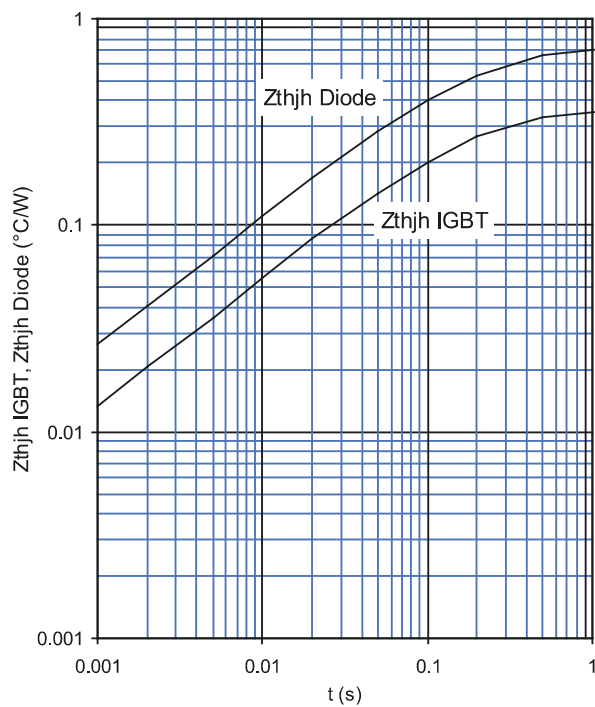


Fig. 13 Typ. Thermal impedance vs time